

2SD2453

Silicon NPN triple diffusion planar type

For high current transfer ratio and power amplification

■ Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage $V_{CE(sat)}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	80	V
Collector-emitter voltage (Base open)	V_{CEO}	60	V
Emitter-base voltage (Collector open)	V_{EBO}	6	V
Collector current	I_C	2	A
Peak collector current *	I_{CP}	4	A
Base current	I_B	1	A
Collector power dissipation	P_C	10	W
		1	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) Non-repetitive peak collector current

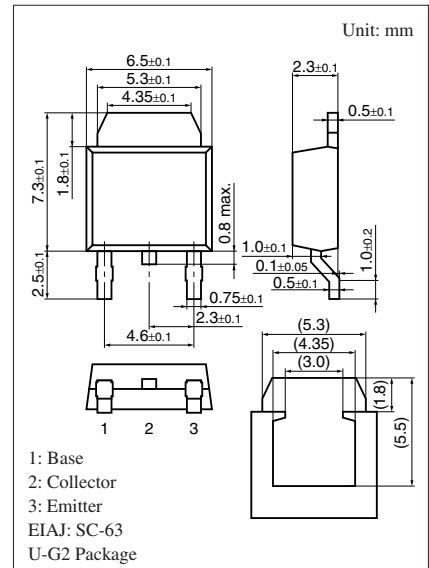
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 25 \text{ mA}$, $I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 80 \text{ V}$, $I_E = 0$			100	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 40 \text{ V}$, $I_B = 0$			100	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 6 \text{ V}$, $I_C = 0$			100	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 4 \text{ V}$, $I_C = 0.5 \text{ A}$	500		2500	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2 \text{ A}$, $I_B = 0.05 \text{ A}$			1	V
Transition frequency	f_T	$V_{CE} = 12 \text{ V}$, $I_C = 0.2 \text{ A}$, $f = 10 \text{ MHz}$		50		MHz

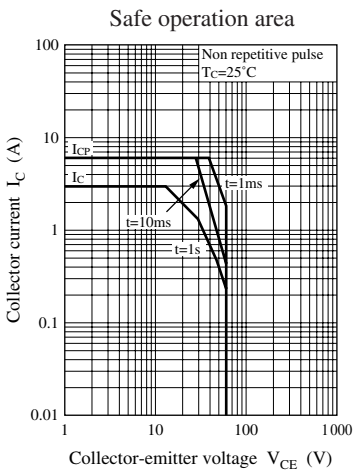
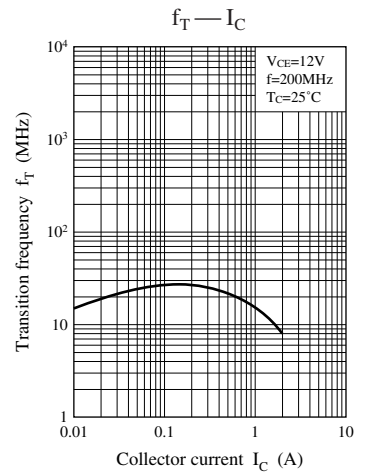
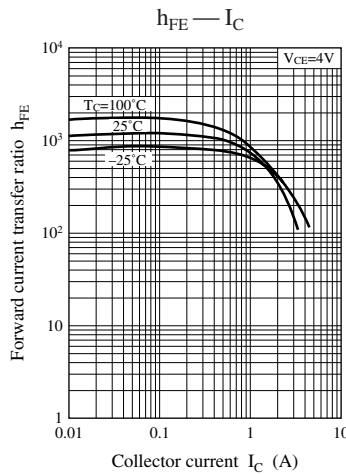
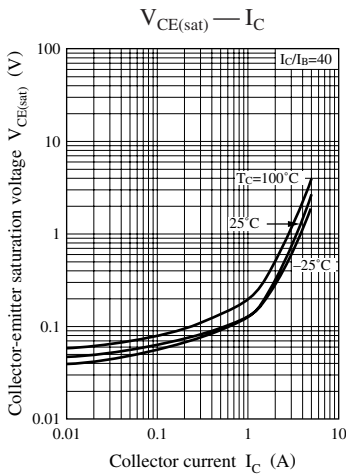
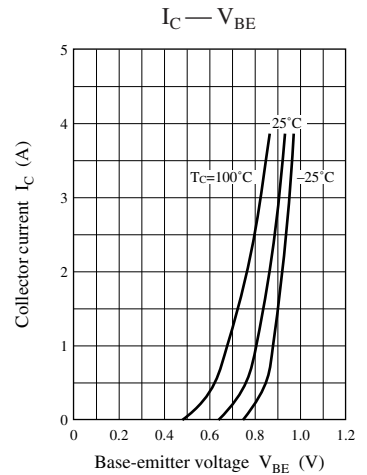
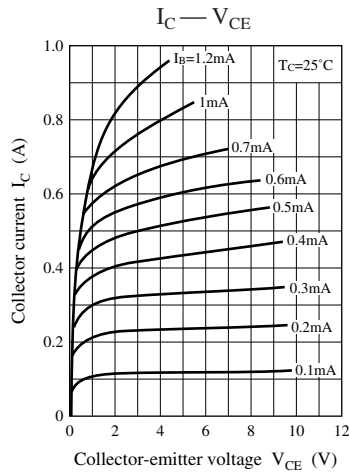
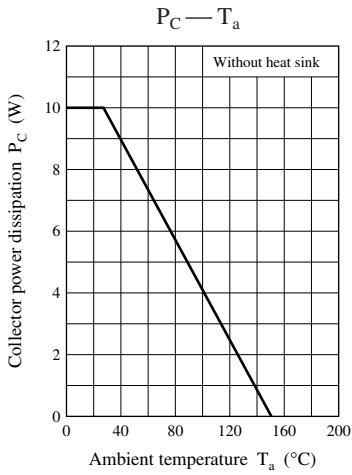
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	R	S
h_{FE}	500 to 1000	800 to 1500	1200 to 2500



Note) Self-supported type package is also prepared.



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